

## HDAE60F60G Fast Recovery Diode

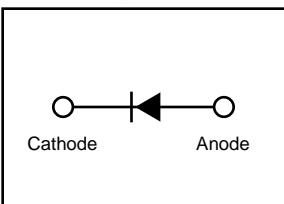
### General Description

With excellent performance in reverse recovery time, switching speed and rated current, HDAE60F60G can be utilized with high voltage power switches for voltage limitation and high-frequency current rectification.

### Features

- High Breakdown Voltage
- High Speed Switching

$V_{RRM} = 600 \text{ V}$   
 $I_F = 60\text{A}$   
 $t_{rr} = 39\text{nS}$



### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	600	V
$V_R$	DC Blocking Voltage		
$I_{F(AV)}$	Average Rectifier Forward Current	60	A
$I_{FSM}$	Non-Rectifier Peak Surge Current @8.3ms	600	A
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	°C

### Electrical Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR}$	Breakdown Voltage	$I_R = 50\mu\text{A}$	600	--	--	V
$V_F$	Forward Voltage	$I_F = 60\text{A}, T_C = 25^\circ\text{C}$	--	1.2	1.5	V
$I_R$	Reverse Current	$V_R = 600\text{V}, T_C = 25^\circ\text{C}$	--	--	50	$\mu\text{A}$
$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{A}, dI/dt = 200\text{A}/\mu\text{s}$	--	39	--	ns

### Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{eJC}$	Junction-to-Case	--	0.8	°C/W

## Typical Characteristics

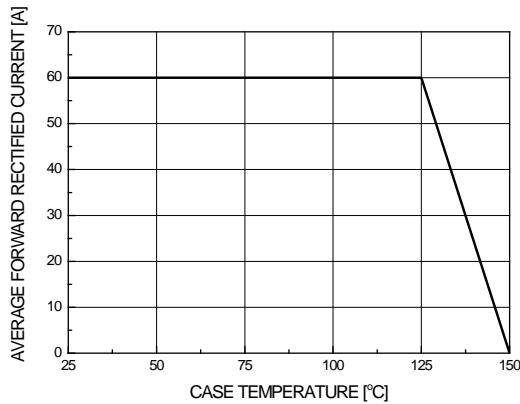


Figure 1. Forward Current Derating Curve

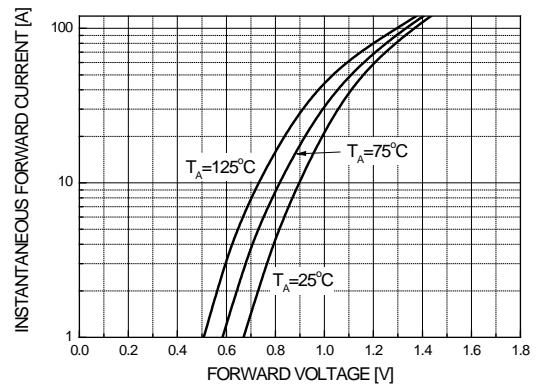


Figure 2. Typical Forward Characteristics

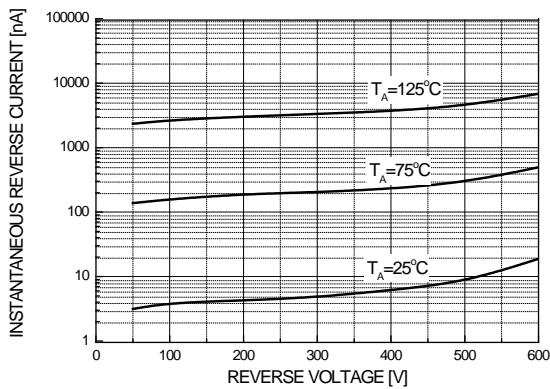


Figure 3. Typical Reverse Characteristics

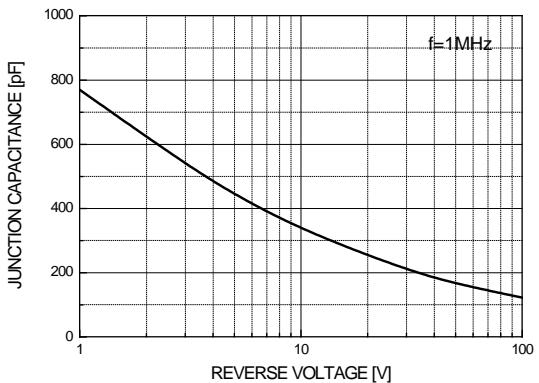


Figure 4. Typical Junction Capacitance

**Package Dimension****TO-247-2L**